

СВ

6

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TDFN-8

(Top View)

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\*\* Samsung Galaxy Tab are trademarks of Samsung Electronics, registered in

TDM

TDP

VDD

Thermal Pad

iconnected to GND

**Pin Configuration** 

U.S. and other countries.

Korea and other countries.

CEN

DM

DP

SMART-CDP

2

3

**USB Host Charger Identification** 

#### **General Description**

The SLG55596AV is a USB device that combines high speed USB switches with a USB host charger (dedicated charger) identification circuit. The device supports both the latest USB Battery Charging Specification Revision 1.2 including data contact detection and a set resistor bias for Apple\* compliant devices as well as legacy USB D+/D- short detection using data line pull-up.

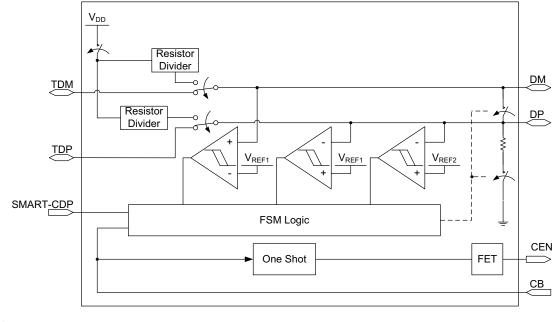
The SLG55596AV can also support CDP mode (FAST charging and data communication available mode if smartphone can support CDP mode).

The SLG55596AV can also support low speed / full speed mouse/keyboard wake-up from S3 mode.

#### **Features**

- · High Speed USB Switching
- · Low 4.0 pF (typ) On Capacitance
- Low 4.0 Ω (typ) On Resistance
- Low 0.5 Ω (typ) On Resistance Flatness
- 4.5 V to 5.5 V Supply Range
- · Low Supply Current
- · Automatic Current-Limit Switch Control
- Automatic USB Charger Identification Circuit
- CDP Support (active USB 2.0 data communication with • 1.5 A charging)
- Apple iPad\* @ 2.4 A charging current support
- Automatic CDP/SDP mode support with SMART-CDP=1 for "Always Data Communication"
- Chinese Telecom Standard YD/T 1591-2009 specification ٠ support
- Samsung Galaxy Tab\*\* charge scheme support
- Pb-Free / RoHS Compliant / Halogen-Free
- TDFN-8 Package

#### **Block Diagram**



#### 8-Feb-2022

CFR0011-120-01



# USB Host Charger Identification

## **Pin Description**

Pin #	Pin Name	Туре	Pin Description
1	CEN	Output	N-FET Open Drain Output. Current Limit Switch (CLS) Control Output. CB changes from 0 to 1 or 1 to 0. CEN will be low for 2 seconds (typ)
2	DM	Input/Output	USB Connector D-
3	DP	Input/Output	USB Connector D+
4	SMART-CDP	Input	Input Control logic (see truth table)
5	VDD	PWR	Power Supply. Connect a $0.1\mu\text{F}$ capacitor between VDD and GND as close as possible to the device.
6	TDP	Input/Output	Host USB Transceiver D+ Connection
7	TDM	Input/Output	Host USB Transceiver D- Connection
8	СВ	Input	Switch Control Bit 0 = auto-detection charger identification active 1 = charging downstream port with active USB2.0 data communication mode with 1.5 A support
9	Thermal Pad	GND	Ground

## **Truth Table**

СВ	SMART-CDP	Function
0	0 or 1	DCP autodetect with mouse/keyboard wakeup (Pin 4 = 0 or 1)
1	0	S0 charging with SDP only
1	1	S0 charging with CDP or SDP only (depending on external device) And, when Non-CDP phone is plugged in, the CDP mode will be changed automatically to SDP mode during handshaking protocol for supporting data communication.

## **Ordering Information**

Part Number	Туре
SLG55596AV	TDFN-8
SLG55596AVTR	TDFN-8 - Tape and Reel

## **USB Host Charger Identification**

### **Absolute Maximum Ratings**

Parameter	Min.	Max.	Unit
Supply Voltage	-0.3	6.0	V
Continuous Current into any terminal	-30	+30	mA
Continuous Power Dissipation		954	mW
Operating Temperature Range	-40	85	۵°
Junction Temperature		150	۵°
Storage Temperature Range	-65	150	°C
Lead Temperature (Soldering, 10s)		260	°C
Note: Stresses greater than those listed under "Absolute Maximum Ratings"	' may cause permanent dar	nage to the device	This is a stress ratin

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### **Electrical Characteristics - Power Supply**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25 °C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V	Power Supply Pango	V <sub>CB</sub> > V <sub>IH</sub>	4.5	5.0	5.5	V
V <sub>DD</sub>	Power Supply Range	V <sub>CB</sub> = 0 V	4.75		5.25	V
	Supply Current V <sub>DD</sub> = 5 V	CB = LOW, SMART-CDP = X (au- todetect with wakeup)		140	160	μA
I <sub>DD</sub>		CB = HIGH, SMART-CDP = LOW (SDP)		20	30	μA
		CB = HIGH, SMART-CDP = HIGH (CDP)		30	50	μA



## **USB Host Charger Identification**

### **Electrical Characteristics - Analog Switch**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25  $^\circ C$  (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V <sub>DP</sub> , V <sub>DM</sub>	Analog signal Range		0		V <sub>DD</sub>	V
		$V_{DD}$ = -0.4 V to 0.4 V, I = 10 mA		3.5		Ω
R <sub>ON</sub>	On Resistance TDP/TDM Switch	$V_{DP} = V_{DM} = 0 V \text{ to } 3.3 V$ $V_{DD} = 5 V$		4.0	7	Ω
$\Delta R_{ON}$	On Resistance Match between channels TDP/TDM Switch	$V_{DD} = 5.0V$ $V_{DP} = V_{DM} = 400 \text{ mV}$ $I_{DP} = I_{DM} = 10 \text{ mA}$		0.1	-	Ω
R <sub>FLAT</sub>	On Resistance flatness TDP/TDM Switch	$V_{DD} = 5.0 V$ $V_{DP} = V_{DM} = 0 V \text{ to } V_{DD}$ $I_{DP} = I_{DM} = 10 \text{ mA}$		0.5	-	Ω
R <sub>SHORT</sub>	On Resistance of TDP/TDM Short	V <sub>CB</sub> = 0 V V <sub>DP</sub> = 1 V I <sub>DP</sub> = I <sub>DM</sub> = 10 mA		50	70	Ω
I <sub>TDPOFF</sub> , I <sub>TDMOFF</sub>	Off-Leakage Current	$V_{DD} = 3.6V V_{DP} = V_{DM} = 0.3 V \text{ to } 3.3 V V_{TDP} = V_{TDM} = 3.3 V \text{ to } 0.3 V V_{CB} = 0 V$	-250		250	nA
I <sub>DPON</sub> , I <sub>DMON</sub>	Off-Leakage Current	$V_{DD} = 3.6 V$ $V_{DP} = V_{DM} = 3.3 V \text{ to } 0.3 V$ $V_{CB} = V_{DD}$	-250		250	nA

## **Electrical Characteristics - Dynamic Performance**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25  $^\circ C$  (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
T <sub>ON</sub>	Turn On Time	V <sub>TDP</sub> or V <sub>TDM</sub> = 1.5 V R <sub>L</sub> = 300 Ω C <sub>L</sub> = 35 pF	'	20	100	μs
T <sub>OFF</sub>	Turn Off Time	V <sub>TDP</sub> or V <sub>TDM</sub> = 1.5 V R <sub>L</sub> = 300 Ω C <sub>L</sub> = 35 pF	'	1	5	μs
T <sub>PLH</sub> , T <sub>PHL</sub>	TDP/TDM Switch Propagation Delay	R <sub>L</sub> = R <sub>S</sub> = 50 Ω		60		ps
T <sub>SKEW</sub>	Output Skew	Skew between DP and DM when connected to TDP and TDM $R_L = R_S = 50 \ \Omega$		40		ps
C <sub>OFF</sub>	TDP/TDM Off-Capacitance	f = 1 MHz	"	2.0		pF
C <sub>ON</sub>	DP/DM On-Capacitance	f = 240 MHz	"	4.0	5.5	pF
BW	-3 dB Bandwidth	R <sub>L</sub> = R <sub>S</sub> = 50 Ω		1000		MHz
V <sub>ISO</sub>	Off-Isolation	$V_{TDP}$ , $V_{DP}$ = 0 dBm R <sub>L</sub> = R <sub>S</sub> =50 Ω f = 250 MHz		-20		dB
V <sub>CT</sub>	Crosstalk	$V_{TDP}$ , $V_{DP}$ = 0 dBm R <sub>L</sub> = R <sub>S</sub> = 50 Ω f = 250 MHz		-25		dB

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**USB Host Charger Identification** 

### **Electrical Characteristics - Internal Resistors**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25 °C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
R <sub>PD</sub>	DP/DM Short Pull-down		350	500	700	kΩ
RT <sub>RP</sub>	RP1/RP2 Ratio		0.8544	0.863	0.872	Ratio
R <sub>RP</sub>	RP1 + RP2 Resistance		69.75	93.0	115.18	kΩ
RT <sub>RM</sub>	RM1/RM2 Ratio		0.8544	0.863	0.872	Ratio
R <sub>RM</sub>	RM1 + RM2 Resistance		69.75	93.0	115.18	kΩ

#### **Electrical Characteristics - Logic Input CB**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25 °C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V <sub>IH</sub>	CB Input Logic High		1.4			V
V <sub>IL</sub>	CB Input Logic Low				0.4	V
I <sub>IN</sub>	CB Input Leakage Current	$\begin{array}{l} V_{DD} = 5.5 \text{ V} \\ 0 \leq V_{CB} \leq V_{IL} \text{ or } V_{IH} \leq V_{CB} \leq V_{DD} \end{array}$	-1		1	μA

#### **Electrical Characteristics - Logic Input SMART-CDP**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_{A}$  = 25  $^{\circ}C$  (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V <sub>IH</sub>	SMART-CDP input Logic High		3.0			V
V <sub>IL</sub>	SMART-CDP input Logic Low				0.8	V
I <sub>IN</sub>	SMART-CDP Input Leakage Current	V <sub>DD</sub> = 5.5V 0 V < V <sub>SMART-CDP</sub> < V <sub>IL</sub> or V <sub>IH</sub> < V <sub>SMART-CDP</sub> < V <sub>DD</sub>	-1		1	μA

#### **Electrical Characteristics - CEN Outputs**

 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25 °C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
T <sub>VBT</sub>	V <sub>BUS</sub> Toggle Time	CB = Logic 0 to Logic 1 or Logic 1 to Logic 0	1.5	2.0	2.5	s
V <sub>OL_CEN</sub>	CEN Output Logic Low Voltage	CB = Logic 0 to Logic 1 I <sub>SINK</sub> = 2 mA			0.4V	V
I <sub>OUT_CEN</sub>	CEN Output Leakage Current	$V_{DD}$ = 5.5 V $V_{CEN}$ = 5.5 V or CEN deasserted			1	μA

### **Electrical Characteristics - ESD Protection**

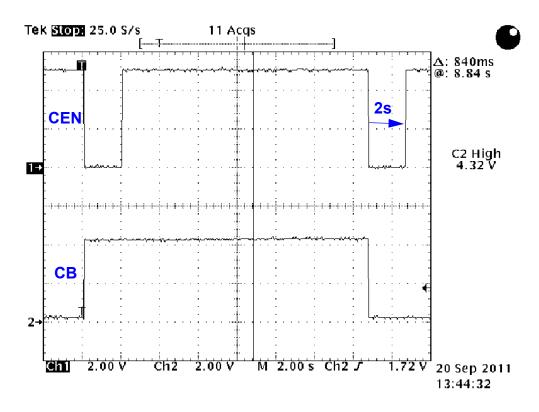
 $V_{DD}$  = 4.5 V to 5.5 V,  $T_A$  = 25 °C (unless specified otherwise)

Parameter	Description	Condition/Note	Min.	Тур.	Max.	Unit
V <sub>ESD</sub>	ESD Protection Level (DP and DM Only)	Human Body Model		±8		kV
V <sub>ESD</sub>	ESD Protection Level (All other pins)	Human Body Model		±2		kV



**USB Host Charger Identification** 

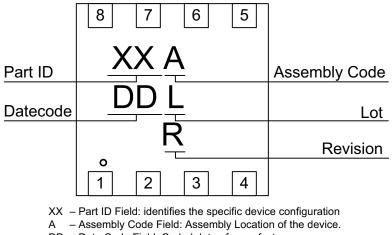
### **CEN Function Waveform**





## **USB Host Charger Identification**

### Package Top Marking System Definition



DD - Date Code Field: Coded date of manufacture

L – Lot Code: Designates Lot #

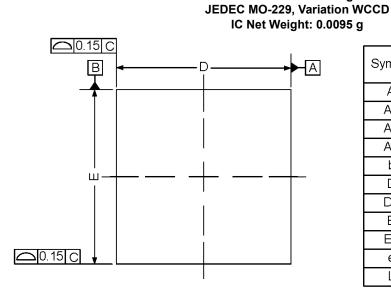
R - Revision Code: Device Revision

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		LC	5		е	e	

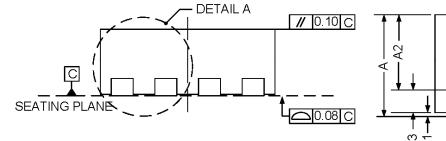


## **USB Host Charger Identification**

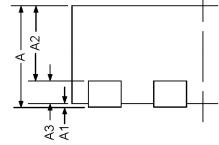
## **Package Drawing and Dimensions**



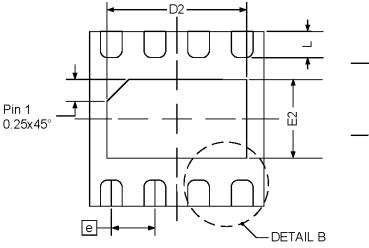
Symbol	Min (mm)	NOM (mm)	Max (mm)	
Α	0.70	0.75	0.80	
A1	0.00		0.05	
A2	A2			
A3		0.20		
b	0.20	0.25	0.30	
D	1.90	2.00	2.10	
D2	1.50	1.60	1.70	
E	1.90	2.00	2.10	
E2	0.80	0.90	1.00	
е	0.50 BSC			
L	0.20	0.30	0.40	

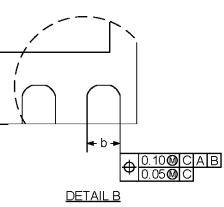


8 Lead TDFN Package









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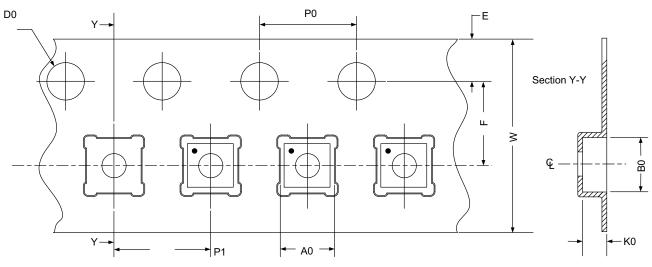
## **USB Host Charger Identification**

### **Tape and Reel Specifications**

Deekere	Nominal		Max Units		Reel &	Leader (min)		Trailer (min)		Таре	Part
Package Type	# of Pins	Package Size [mm]	per Reel	per Box	A Hub Size (mm)	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
TDFN 8L Green	8	2 x 2 x 0.75	3,000	3,000	178 / 60	100	400	100	400	8	4

## **Carrier Tape Drawing and Dimensions**

Package Type	PocketBTM Length	PocketBTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge		Tape Width
	A0	В0	K0	P0	P1	D0	E	F	w
TDFN 8L Green	2.3	2.3	1.05	4	4	1.55	1.75	3.5	8



Refer to EIA-481 specification

## **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 3.00 mm<sup>3</sup> (nominal). More information can be found at www.jedec.org.

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## **Revision History**

Date	Version	Change
2/8/2022 1.02 Updated Company name and logo Fixed typos		
5/27/2020	20 1.01 Updated Style and formatting	
4/22/2014	1.00	Production Release

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